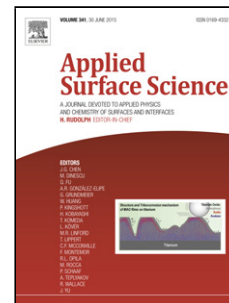


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Title: HfO_2 Gate Dielectric on Ge (111) with Ultrathin Nitride Interfacial Layer formed by Rapid Thermal NH_3 Treatment

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Highlights

1. The GeON/HfO₂ gate stack is formed on Germanium (111) substrate.
2. The Rapid thermal nitridation was carried out by using NH₃.
3. The GeON forms the stable interface between high-k and Ge substrate.
4. The results show the improvement in k value and EOT due to NH₃ pre deposition annealing.
5. The effect of post metallization annealing was studied on different parameters of Ge MOS devices.

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